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TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74AC10P,TC74AC10F,TC74AC10FN

Triple 3-Input NAND Gate

The TC74AC10 is an advanced high speed CMOS 3-INPUT NAND GATE fabricated with silicon gate and double-layer metal wiring C²MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

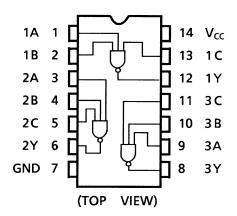
Features

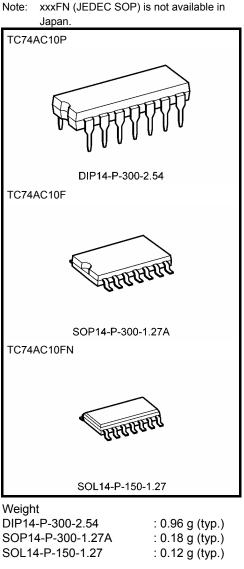
- High speed: $t_{pd} = 5.0$ ns (typ.) at V_{CC} = 5 V
- Low power dissipation: $I_{CC} = 4 \mu A (max)$ at $Ta = 25^{\circ}C$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Symmetrical output impedance: |IOH| = IOL = 24 mA (min)

Capability of driving 50 Ω transmission lines.

- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: V_{CC} (opr) = 2 to 5.5 V
- Pin and function compatible with 74F10

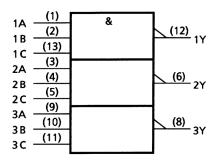
Pin Assignment





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IEC Logic Symbol



Truth Table

А	В	С	Y
L	Х	Х	Н
Х	L	Х	Н
Х	Х	L	Н
Н	Н	Н	L

X: Don't care

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	–0.5 to 7.0	V
DC input voltage	V _{IN}	–0.5 to V _{CC} + 0.5	V
DC output voltage	V _{OUT}	-0.5 to V _{CC} + 0.5	V
Input diode current	IIК	±20	mA
Output diode current	I _{OK}	±50	mA
DC output current	IOUT	±50	mA
DC V _{CC} /ground current	Icc	±100	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T _{stg}	–65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C should be applied up to 300 mW.

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	2.0 to 5.5	V	
Input voltage	V _{IN}	0 to V _{CC}	V	
Output voltage	V _{OUT}	0 to V _{CC}	V	
Operating temperature	T _{opr}	-40 to 85	°C	
Input rise and fall time	dt/dV	0 to 100 (V_{CC} = 3.3 \pm 0.3 V)	ns/V	
	ut/uv	0 to 20 (V_{CC} = 5 \pm 0.5 V)	115/ V	

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics Symbol		Test Condition V _{CC} (V)			Ta = 25°C			Ta = -40 to 85°C		Unit	
						Min	Тур.	Max	Min	Max	Offic
					2.0	1.50		_	1.50		
High-level input voltage	VIH		_		3.0	2.10	—	—	2.10		V
					5.5	3.85	—	—	3.85	—	
					2.0	_	_	0.50	_	0.50	
Low-level input voltage	VIL	—		3.0	—	—	0.90	_	0.90	V	
					5.5	_	_	1.65		1.65	
	Vон				2.0	1.9	2.0		1.9	_	
		V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA		3.0	2.9	3.0	—	2.9	—	
High-level output					4.5	4.4	4.5	_	4.4	_	v
voltage			I _{OH} = -4 mA		3.0	2.58	—	—	2.48	—	v
			I _{OH} = -24 mA		4.5	3.94	—	—	3.80	—	
			I _{OH} = -75 mA	(Note)	5.5	_		_	3.85		
	Vol	V _{IN} = VIH			2.0	—	0.0	0.1	—	0.1	
			$I_{OL} = 50 \ \mu A$		3.0	—	0.0	0.1	—	0.1	
Low-level output voltage					4.5	_	0.0	0.1	_	0.1	V
			$I_{OL} = 12 \text{ mA}$		3.0	—	—	0.36	—	0.44	v
			I _{OL} = 24 mA		4.5	—	—	0.36	—	0.44	
			$I_{OL} = 75 \text{ mA}$	(Note)	5.5	_	_	_	_	1.65	
Input leakage current	I _{IN}	$V_{IN} = V_{CC}$ or GND			5.5	_	—	±0.1	_	±1.0	μΑ
Quiescent supply current	ICC	$V_{IN} = V_{CC}$ or GND			5.5	_	_	4.0		40.0	μΑ

Note: This spec indicates the capability of driving 50 Ω transmission lines.

One output should be tested at a time for a 10 ms maximum duration.

AC Characteristics (C_L = 50 pF, R_L = 500 Ω , input: t_r = t_f = 3 ns)

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit
			V _{CC} (V)	Min	Тур.	Max	Min	Max	
Propagation delay time	t _{pLH}	_	$\textbf{3.3}\pm\textbf{0.3}$	_	7.6	13.0	1.0	15.0	ns
	t _{pHL}		5.0 ± 0.5	—	6.1	8.6	1.0	9.9	
Input capacitance	C _{IN}	—		_	5	10	_	10	pF
Power dissipation capacitance	C _{PD} (Note)	_			70				pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

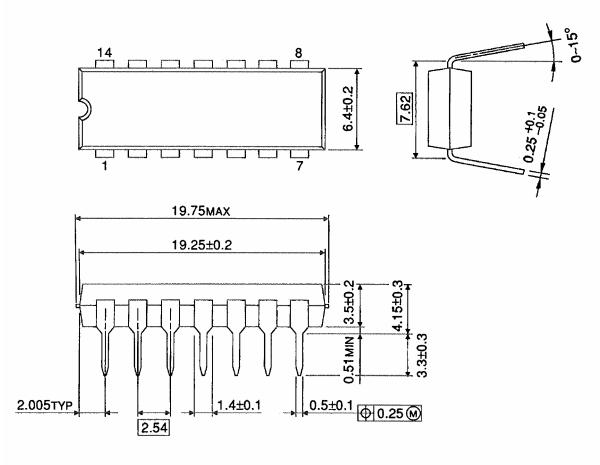
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/3$ (per gate)

Package Dimensions

DIP14-P-300-2.54

Unit : mm



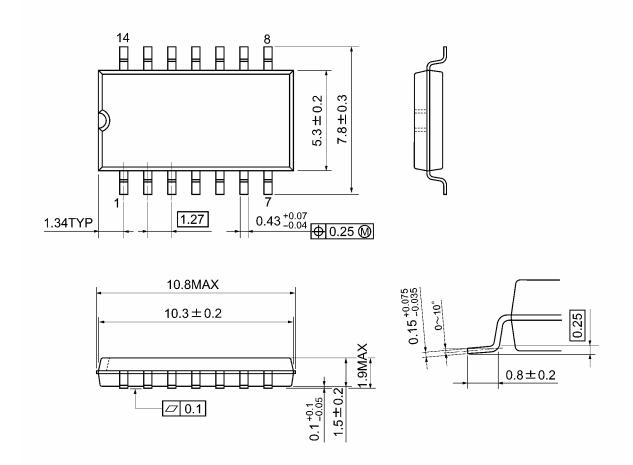
Weight: 0.96 g (typ.)

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Package Dimensions

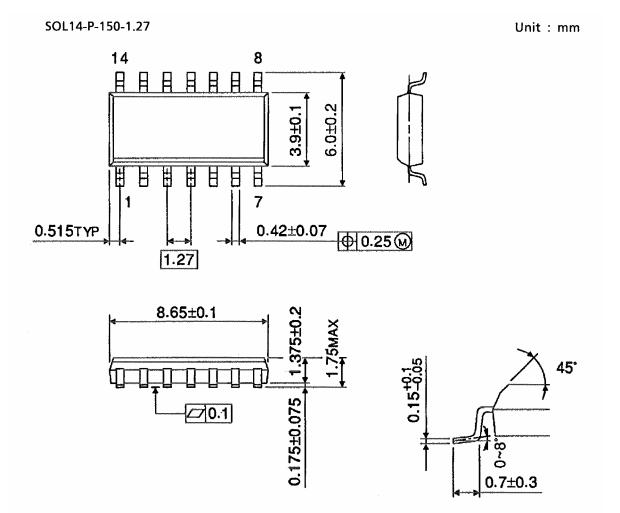
SOP14-P-300-1.27A

Unit: mm



Weight: 0.18 g (typ.)

Package Dimensions (Note)



Note: This package is not available in Japan.

Weight: 0.12 g (typ.)

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20070701-EN GENERAL

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